

# 2N6387, 2N6388

## Plastic Medium-Power Silicon Transistors

These devices are designed for general-purpose amplifier and low-speed switching applications.

### Features

- High DC Current Gain –  $h_{FE} = 2500$  (Typ) @  $I_C = 4.0$  Adc
- Collector–Emitter Sustaining Voltage – @ 100 mAdc  
 $V_{CEO(sus)} = 60$  Vdc (Min) – 2N6387  
 $= 80$  Vdc (Min) – 2N6388
- Low Collector–Emitter Saturation Voltage –  
 $V_{CE(sat)} = 2.0$  Vdc (Max) @  $I_C = 5.0$  Adc – 2N6387, 2N6388
- Monolithic Construction with Built–In Base–Emitter Shunt Resistors
- TO–220AB Compact Package
- These Devices are Pb–Free and are RoHS Compliant\*

### MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	60 80	Vdc
Collector–Base Voltage	$V_{CB}$	60 80	Vdc
Emitter–Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current – Continuous – Peak	$I_C$	10 15	A dc
Base Current	$I_B$	250	mA dc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	65 0.52	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	2.0 0.016	W W/ $^\circ\text{C}$
Operating and Storage Junction, Temperature Range	$T_J, T_{stg}$	–65 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Indicates JEDEC Registered Data.

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	1.92	$^\circ\text{C/W}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$

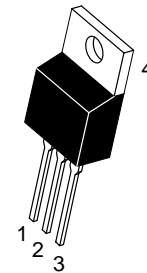
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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## DARLINGTON NPN SILICON POWER TRANSISTORS 8 AND 10 AMPERES 65 WATTS, 60 – 80 VOLTS



TO–220  
CASE 221A  
STYLE 1

### MARKING DIAGRAM



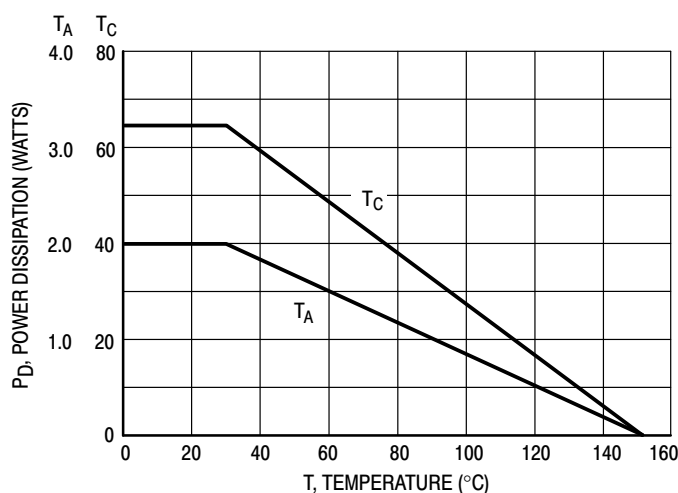
2N638x = Device Code  
x = 7 or 8

G = Pb–Free Package  
A = Assembly Location  
Y = Year  
WW = Work Week

### ORDERING INFORMATION

Device	Package	Shipping
2N6387G	TO–220 (Pb–Free)	50 Units / Rail
2N6388G	TO–220 (Pb–Free)	50 Units / Rail

## 2N6387, 2N6388



**Figure 1. Power Derating**

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 2)

Characteristic	Symbol	Min	Max	Unit	
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Sustaining Voltage (Note 3) ( $I_C = 200\text{ mA}$ , $I_B = 0$ )	2N6387 2N6388	$V_{CEO(sus)}$	60 80	– –	Vdc
Collector Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 80\text{ Vdc}$ , $I_B = 0$ )	2N6387 2N6388	$I_{CEO}$	– –	1.0 1.0	mA
Collector Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB(off)} = 1.5\text{ Vdc}$ ) ( $V_{CE} = 80\text{ Vdc}$ , $V_{EB(off)} = 1.5\text{ Vdc}$ ) ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB(off)} = 1.5\text{ Vdc}$ , $T_C = 125^\circ\text{C}$ ) ( $V_{CE} = 80\text{ Vdc}$ , $V_{EB(off)} = 1.5\text{ Vdc}$ , $T_C = 125^\circ\text{C}$ )	2N6387 2N6388 2N6387 2N6388	$I_{CEX}$	– – – –	300 300 3.0 3.0	$\mu\text{A}$ mA
Emitter Cutoff Current ( $V_{BE} = 5.0\text{ Vdc}$ , $I_C = 0$ )		$I_{EBO}$	–	5.0	mA
<b>ON CHARACTERISTICS (Note 3)</b>					
DC Current Gain ( $I_C = 5.0\text{ A}$ , $V_{CE} = 3.0\text{ Vdc}$ ) ( $I_C = 1.0\text{ A}$ , $V_{CE} = 3.0\text{ Vdc}$ )	2N6387, 2N6388 2N6387, 2N6388	$h_{FE}$	1000 100	20,000 –	–
Collector–Emitter Saturation Voltage ( $I_C = 5.0\text{ A}$ , $I_B = 0.01\text{ A}$ ) ( $I_C = 1.0\text{ A}$ , $I_B = 0.1\text{ A}$ )	2N6387, 2N6388 2N6387, 2N6388	$V_{CE(sat)}$	– –	2.0 3.0	Vdc
Base–Emitter On Voltage ( $I_C = 5.0\text{ A}$ , $V_{CE} = 3.0\text{ Vdc}$ ) ( $I_C = 1.0\text{ A}$ , $V_{CE} = 3.0\text{ Vdc}$ )	2N6387, 2N6388 2N6387, 2N6388	$V_{BE(on)}$	– –	2.8 4.5	Vdc
<b>DYNAMIC CHARACTERISTICS</b>					
Small–Signal Current Gain ( $I_C = 1.0\text{ A}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f_{test} = 1.0\text{ MHz}$ )		$ h_{fe} $	20	–	–
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )		$C_{ob}$	–	200	pF
Small–Signal Current Gain ( $I_C = 1.0\text{ A}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )		$h_{fe}$	1000	–	–

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates JEDEC Registered Data.

3. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

# 2N6387, 2N6388

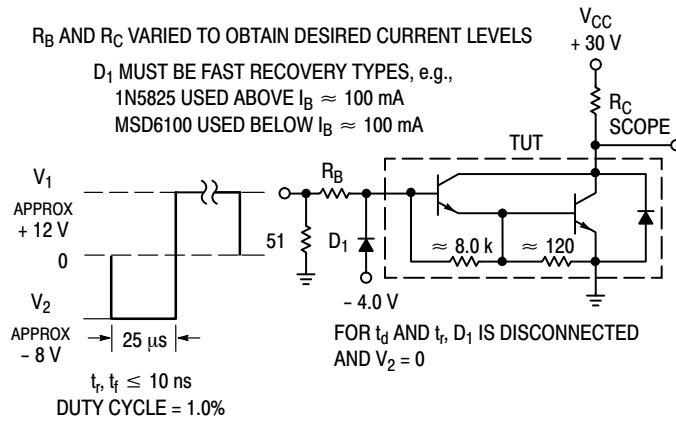


Figure 2. Switching Times Test Circuit

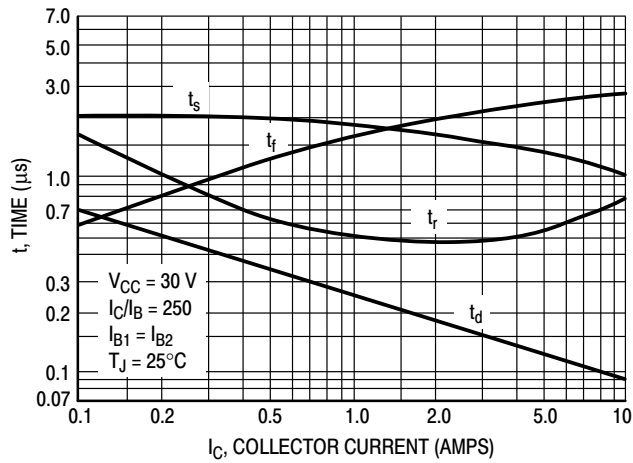


Figure 3. Switching Times

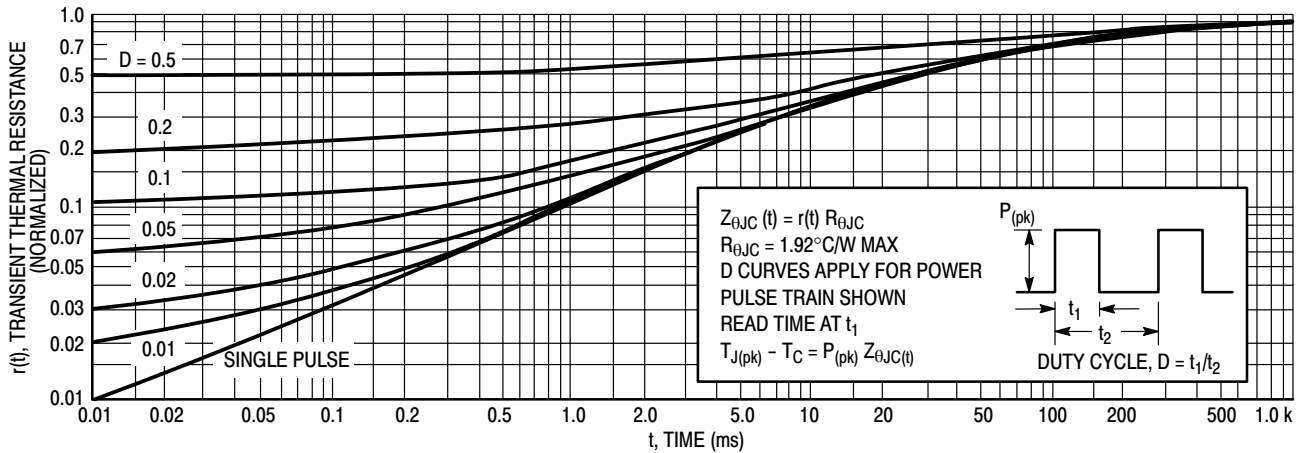


Figure 4. Thermal Response

## 2N6387, 2N6388

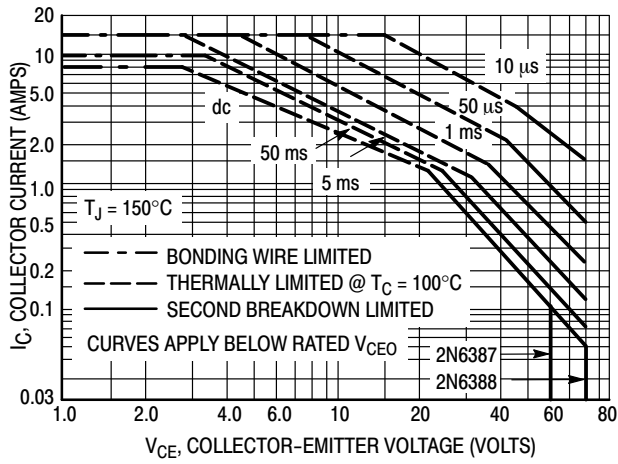


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown

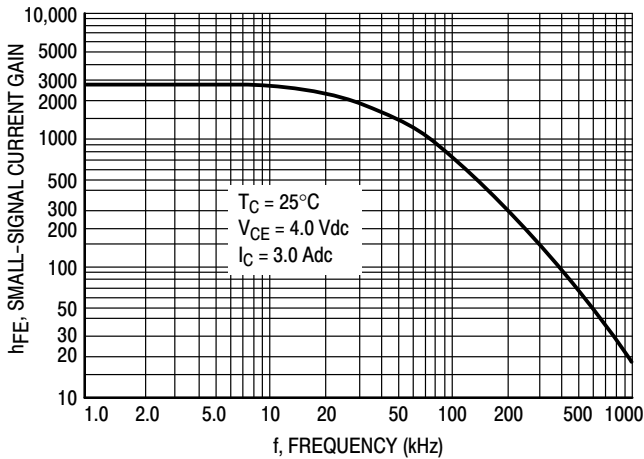


Figure 6. Small-Signal Current Gain

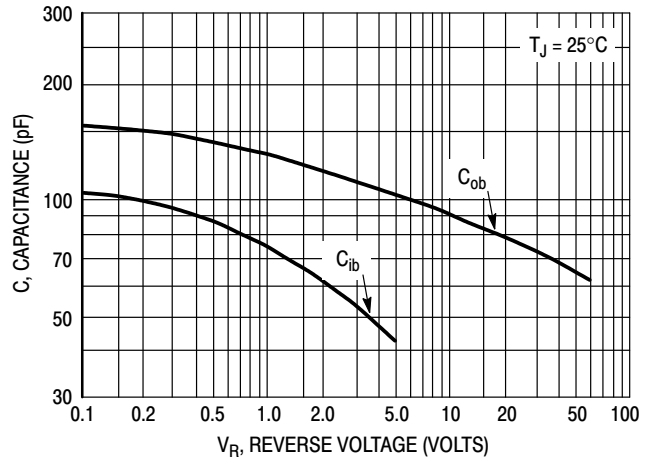


Figure 7. Capacitance

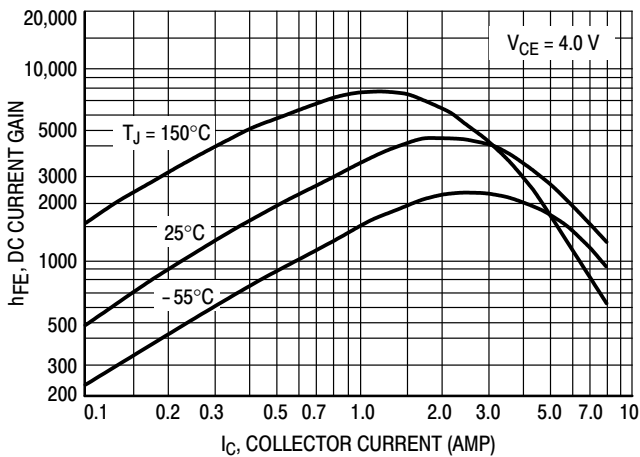


Figure 8. DC Current Gain

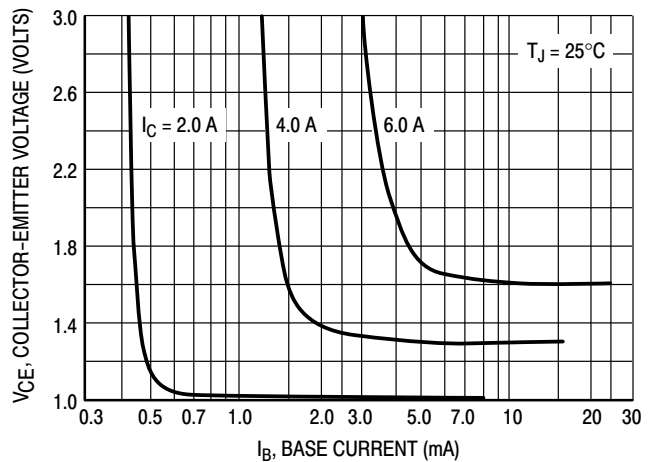


Figure 9. Collector Saturation Region

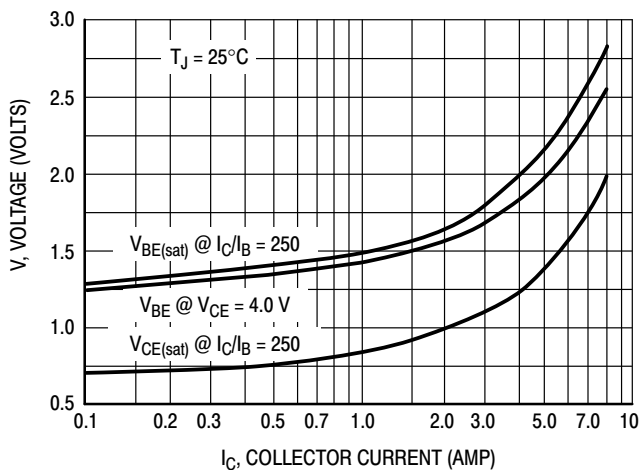


Figure 10. "On" Voltages

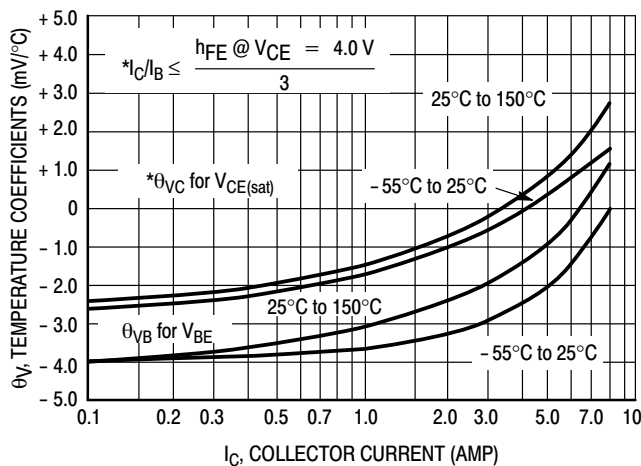


Figure 11. Temperature Coefficients

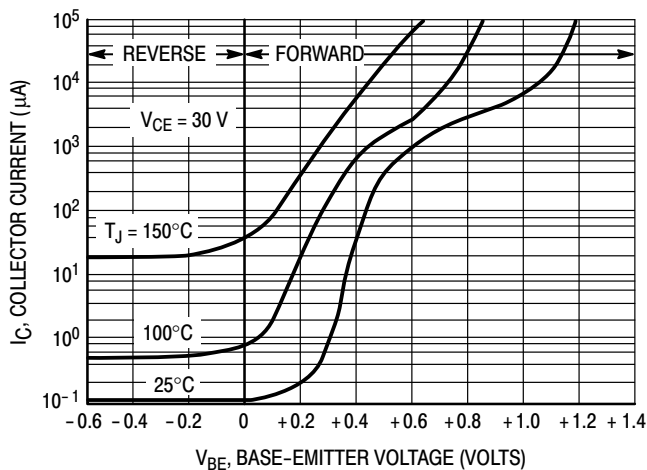


Figure 12. Collector Cut-Off Region

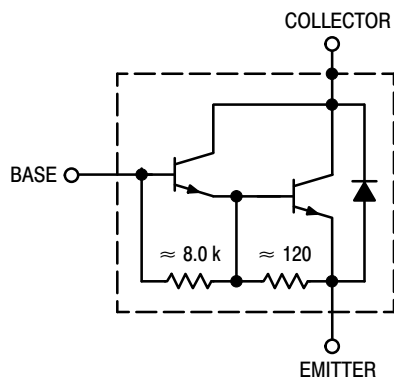
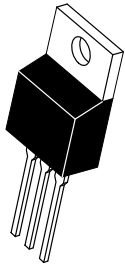


Figure 13. Darlington Schematic

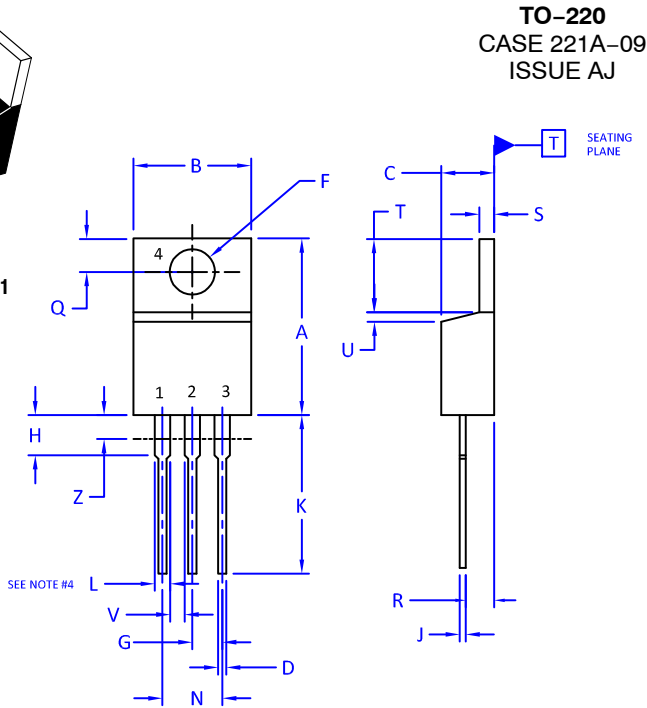
# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1



TO-220  
CASE 221A-09  
ISSUE AJ

DATE 05 NOV 2019

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 2:

- PIN 1. BASE
- 2. EMITTER
- 3. COLLECTOR
- 4. EMITTER

STYLE 3:

- PIN 1. CATHODE
- 2. ANODE
- 3. GATE
- 4. ANODE

STYLE 4:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. MAIN TERMINAL 2

STYLE 5:

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

STYLE 6:

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

STYLE 7:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

STYLE 8:

- PIN 1. CATHODE
- 2. ANODE
- 3. EXTERNAL TRIP/DELAY
- 4. ANODE

STYLE 9:

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 10:

- PIN 1. GATE
- 2. SOURCE
- 3. DRAIN
- 4. SOURCE

STYLE 11:

- PIN 1. DRAIN
- 2. SOURCE
- 3. GATE
- 4. SOURCE

STYLE 12:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. NOT CONNECTED

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